



Dual PWM Step-Down Converter in a 2mm x 2mm Package for WCDMA PA and RF Power

General Description

The MAX8896 dual step-down converter is optimized for powering the power amplifier (PA) and RF transceiver in WCDMA handsets. This device integrates a highefficiency PWM step-down converter (OUT1) for medium and low-power transmission, and a $140m\Omega$ (typ) bypass FET to power the PA directly from the battery during high-power transmission. A second highefficiency PWM step-down converter (OUT2) supplies power directly to a high PSRR, low output noise, 200mA low-dropout linear regulator (LDO) to power the RF transceiver.

Fast switching allows the use of small ceramic input and output capacitors while maintaining low ripple voltage. The feedback network is integrated reducing external component count and total solution size. OUT1 uses an analog input driven by an external DAC to control the output voltage linearly for continuous PA power adjustment. At high duty cycle, OUT1 automatically switches to bypass mode, connecting the input to the output through a low-impedance (140m Ω , typ) MOSFET.

OUT2 is a 2MHz fixed-frequency, step-down converter capable of operating at 100% duty cycle. Output accuracy is $\pm 2\%$ over load, line, and temperature. The output of OUT2 is preset to 3.1V to provide power to a 200mA, 2.8V LDO designed for low noise ($16\mu V_{RMS}$, typ), high PSRR (65dB, typ) operation. This configuration provides noise attenuation for the RF transceiver power supply in the 100Hz to 100kHz range.

Other features include separate output enables, low-supply current shutdown, output overcurrent, and overtemperature protection. The MAX8896 is available in a 16-bump, 2mm x 2mm UCSPTM package (0.7mm max height).

Applications

WCDMA/NCDMA Cellular Handsets

Smartphones

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Features

- ◆ PA Step-Down Converter (OUT1)
 - 7.5µs (typ) Settling Time for 0.5V to 1V Output Voltage Change
 - Dynamic Output Voltage Setting from 0.5V to VBATT
 - 140m Ω Bypass PFET and 100% Duty Cycle for Low Dropout
 - 2MHz Switching Frequency Low Output Voltage Ripple
 - 700mA (min) Output Drive Capability
 - 2% Gain Accuracy
 - **Tiny External Components**
- RF Step-Down Converter (OUT2)
 2MHz Fixed Switching Frequency
 - 94% Peak Efficiency
 - 100% Duty Cycle
 - 2% Output Accuracy Over Load, Line, and Temperature
 - 200mA (min) Output Drive Capability Tiny External Components
- **♦ Low-Noise LDO**
 - Guaranteed 200mA Output High 65dB (typ) PSRR Fixed Output Voltage
 - Low Noise (16µVRMS, typ)
- **♦ Simple Logic ON/OFF Controls**
- ♦ Low 0.1µA Shutdown Current
- ♦ 2.7V to 5.5V Supply Voltage Range
- **♦ Thermal Shutdown**
- 2mm x 2mm UCSP Package (4 x 4 Grid)

Ordering Information

PART		PIN-PACKAGE	LDO VOLTAGE		
١	MAX8896EREE+T	16 UCSP (0.5mm pitch)	2.80V		

Note: Device operates over the -40°C to +85°C temperature range.

+Denotes a lead(Pb)-free/RoHS-compliant package. T = Tape and reel.

UCSP is a trademark of Maxim Integrated Products, Inc.

Pin Configurations appear at end of data sheet.

Dual PWM Step-Down Converter in a 2mm x 2mm Package for WCDMA PA and RF Power

ABSOLUTE MAXIMUM RATINGS

VCC, IN1, IN2, PAEN, RFEN1, RFEN2,	
REFIN, OUT2, REFBP to AGND	0.3V to +6.0V
PAOUT to AGND	0.3V to $(V_{IN1} + 0.3V)$
LDO to AGND	$0.3V$ to $(V_{OUT2} + 0.3V)$
IN1, IN2 to V _C C	0.3V to +0.3V
IN1 to IN2	0.3V to +0.3V
PGND1, PGND2 to AGND	
LX1 Current	1A _{RMS}
LX2 Current	1A _{RMS}
IN1 and PAOUT Current	1ARMS

PAOUT, OUT2, LDO Short Circuit to PGN	D1,
PGND2	Continuous
Continuous Power Dissipation ($T_A = +70^{\circ}$	
16-Bump UCSP (derate 12.5mW/°C abo	
Junction-to-Ambient Thermal Resistance (θ _{JA}) (Note 1)96°C/W
Junction Temperature	
Storage Temperature Range	
Bump Temperature (soldering, reflow)	+260°C

Note 1: Package thermal resistances were obtained using the method described in JEDEC specification JESD51-7, using a four-layer board. For detailed information on package thermal considerations, refer to www.maxim-ic.com/thermal-tutorial.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

(VCC = V_{IN1} = V_{IN2} = V_{PAEN} = V_{RFEN1} = V_{RFEN2} = 3.6V, V_{REFIN} = 0.72V, T_A = -40°C to +85°C, typical values are at T_A = +25°C, unless otherwise noted.) (Note 2)

PARAMETER	CONDITI	MIN	TYP	MAX	UNITS	
INPUT SUPPLY	W MIN TO		•	MA.		No.
Input Voltage	VCC, VIN1, VIN2	40 M	2.7	-1	5.5	V
Input Undervoltage Threshold	V _{CC} rising, 180mV typical hyste	eresis	2.52	2.63	2.70	V
Shutdown Supply Current	VPAEN = VRFEN1 = VRFEN2 = 0	$T_A = +25^{\circ}C$		0.1	4	μA
Shutdown Supply Current	VPAEN = VRFEN1 = VRFEN2 = 0	$T_A = +85^{\circ}C$		0.1		
LOGIC CONTROL	100	21 C				-41
PAEN, RFEN1, RFEN2 Logic Input High Voltage	2.7V ≤ V _{CC} ≤ 5.5V		1.3			V
PAEN, RFEN1, RFEN2 Logic Input Low Voltage	2.7V ≤ V _{CC} ≤ 5.5V	100 7 CO		×1	0.4	V
PAEN, RFEN1, RFEN2 Internal Pulldown Resistor	May TAI Jan of Co.		400	800	1600	kΩ
PAEN, RFEN1, RFEN2 Logic		$T_A = +25^{\circ}C$		0.01 1		μΑ
Input Current V _{IL} = 0		$T_A = +85^{\circ}C$		0.1		
REFBP	N. T. T.		10		.4	
REFBP Output Voltage	0μA ≤ IREFBP ≤ 1μA		1.237	1.250	1.263	V
THERMAL PROTECTION					. 1	
Thermal Shutdown	T _A rising, 20°C typical hysteres	is	20 1 6	+160		°C
OUT1	ON.					1
Quiescent Supply Current	VRFEN1 = VRFEN2 = 0V, IPA = 0A, no switching		1001	155	M.	μΑ
	p-channel MOSFET switch, I _{LX}	1 = -200mA	11.	0.16 0.40		
On-Resistance	n-channel MOSFET rectifier, ILX	100	0.17	0.40	Ω	
Load Regulation	R _L is the inductor resistance		RL/2		V/A	
LV1 Lookogo Current	rent V _{IN1} = 5.5V, V _I x ₁ = 0V			0.1 5		
LX1 Leakage Current	VIN1 = 9.5V, $VLX1 = UV$	$T_A = +85^{\circ}C$	W.			μΑ

Dual PWM Step-Down Converter in a 2mm x 2mm Package for WCDMA PA and RF Power

ELECTRICAL CHARACTERISTICS (continued)

 $(V_{CC} = V_{IN1} = V_{IN2} = V_{PAEN} = V_{RFEN1} = V_{RFEN2} = 3.6V, V_{REFIN} = 0.72V, T_A = -40^{\circ}C$ to +85°C, typical values are at $T_A = +25^{\circ}C$, unless otherwise noted.) (Note 2)

PARAMETER	CONDITIONS			TYP	MAX	UNITS	
Peak Current Limit (p-Channel MOSFET)	COMPLEM			1450	1700	mA	
Valley Current Limit (n-Channel MOSFET)	COM TAI			1350	1600	mA	
Minimum On-Time	0 , 40 p. 44			70	~()	ns	
Minimum Off-Time				50	1.0	ns	
Power-Up Delay	From VPAEN rising to VLX1 ri	sing		50	75	μs	
OUT1 REFIN				No			
Common-Mode Range	41 July 21 Co		0.2	~11	1.7	V	
REFIN-to-PAOUT Gain	V _{REFIN} = 0.32V or 1.32V, I _L	<1 = 0A	2.45	2.5	2.55		
Input Resistance				320	10	kΩ	
BYPASS	N 4 100 3 C			MA	101	7 -	
Bypass Mode Threshold	V _{REFIN} falling, 150mV hysteresis			0.396 xV _{CC}	11.	V	
	p-channel MOSFET	T _A = +25°C		0.14		-0	
On-Resistance	$I_{OUT} = -90$ mA $T_{A} = +85$ °C			0.3		Ω	
Bypass Current Limit	V _{PAOUT} = 1.5V	700	1000	1400	mA		
Step-Down Current Limit in Bypass	M. M. M. TOON COM.			1450	1700	mA	
Total Bypass Current Limit	$V_{PAOUT} = V_{LX1} = 1.5V$			2450	3100	mA	
Bypass Off-Leakage Current	V _{CC} = V _{IN1} = 5.5V, V _{PAOUT} = 0V	$T_A = +25^{\circ}C$ $T_A = +85^{\circ}C$		0.01	5	μA	
OUT2		1 100 T			-		
Output Voltage	$I_{OUT2} = 0$ to 150mA, $V_{IN2} = V_{CC} = 3.2V$ to 4.5V	1,100 J. CC	3.038	3.1	3.162	V	
-400, COp. Q		$T_A = +25^{\circ}C$	0.0		5		
OUT2 Leakage Current	$V_{RFEN1} = V_{RFEN2} = 0$	T _A = +85°C		0.1		μA	
No-Load Supply Current	VPAEN = 0V, I _{OUT2} = 0A, switching		COS	2.5		mA	
10 . OD	p-channel MOSFET switch, I _{LX2} = -40mA			300		mΩ	
On-Resistance	n-channel MOSFET rectifier, I _{LX2} = 40mA		-1 CV	300		mΩ	
p-Channel Current-Limit Threshold	1.114		400	450	500	mA	
n-Channel Negative Current Limit	Die All			400		mA	
Maximum Duty Cycle				100	1.7	%	
Minimum Duty Cycle	-0× 10		1 1 100	16.5	7	%	
PWM Frequency			1.8	2.0	2.2	MHz	
Power-Up Delay	From V _{RFEN1} or V _{RFEN2} rising to V _{LX2} rising			35	75	μs	



Dual PWM Step-Down Converter in a 2mm x 2mm Package for WCDMA PA and RF Power

ELECTRICAL CHARACTERISTICS (continued)

 $(V_{CC} = V_{IN1} = V_{IN2} = V_{PAEN} = V_{RFEN2} = 3.6V, \ V_{REFIN} = 0.72V, \ T_{A} = -40^{\circ}C \ to \ +85^{\circ}C, \ typical \ values \ are \ at \ T_{A} = +25^{\circ}C, \ unless \ otherwise \ noted.)$

PARAMETER CONDITIONS			TYP	MAX	UNITS	
LDO	LDO					
Output Voltage, V _{LDO}	V _{OUT2} = 3.1V, I _{LDO} = 1mA to 200mA	2.744	2.800	2.856	V	
Current Limit	V _{OUT2} = 3.1V, V _{LDO} = 0V	250	420	750	mA	
Dropout Voltage	V _{OUT2} = 3.1V, I _{LDO} = 100mA	N.J.	70		mV	
Line Regulation	V _{OUT2} stepped from 3.5V to 5.5V, I _{LDO} = 100mA		2.4	40	mV	
Load Regulation	gulation V _{OUT2} = 3.1V, I _{LDO} stepped from 50µA to 200mA			25		
Power-Supply Rejection ΔVLDO/ΔVOUT2	$V_{OUT2} = 3.1V$, 10Hz to 10kHz, $C_{LDO} = 1\mu F$, $I_{LDO} = 100mA$		65	NY.C	dB	
Output Noise 100Hz to 100kHz, CLDO = 1µF, ILDO = 100mA			16	1003	μV _{RMS}	
Minimum Output Capacitance for Stable Operation 0 < I _{LDO} < 200mA			1	100	μF	
Output Leakage Current	V _{OUT2} = 3.1V, V _{RFEN1} = V _{RFEN2} = 0V		25	No	nA	
Power-Up Delay	From V _{RFEN1} or V _{RFEN2} rising to V _{LDO} rising 50			μs		

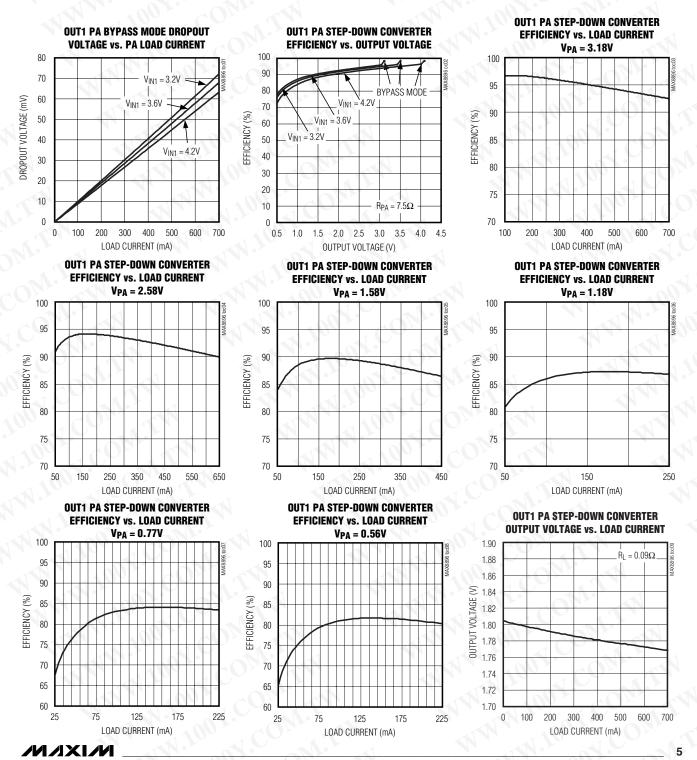
Note 2: All devices are 100% production tested at T_A = +25°C. Limits over the operating temperature range are guaranteed by design.

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Dual PWM Step-Down Converter in a 2mm x 2mm Package for WCDMA PA and RF Power

Typical Operating Characteristics

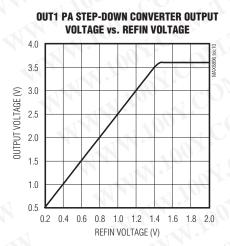
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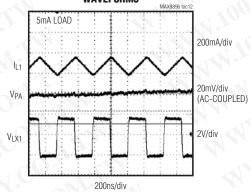
Dual PWM Step-Down Converter in a 2mm x 2mm Package for WCDMA PA and RF Power

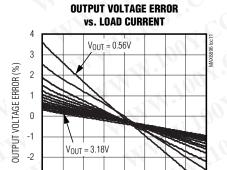
Typical Operating Characteristics (continued)

 $(V_{CC} = V_{IN1} = V_{IN2} = 3.6V, V_{REFIN} = 0.72V, circuit of Figure 3, T_A = +25$ °C, unless otherwise noted.)



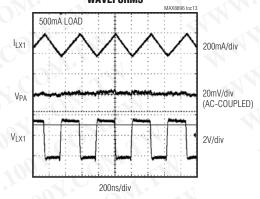
OUT1 LIGHT-LOAD SWITCHING WAVEFORMS

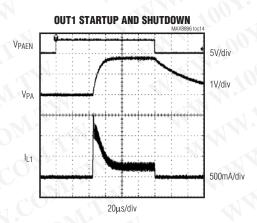




LOAD CURRENT (MA) OUT1 HEAVY-LOAD SWITCHING WAVEFORMS

0 100 200 300 400 500 600 700 800

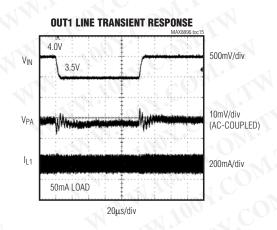


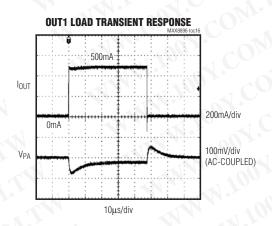


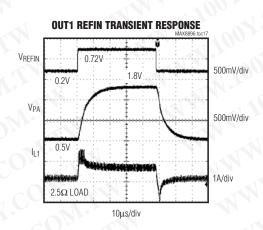
Dual PWM Step-Down Converter in a 2mm x 2mm Package for WCDMA PA and RF Power

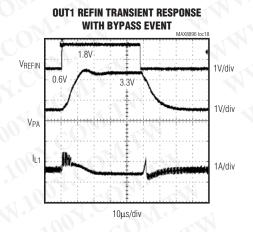
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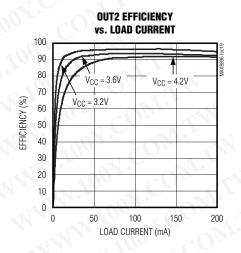
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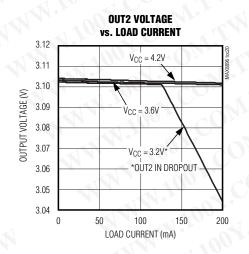








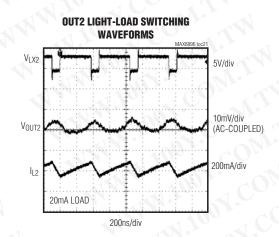


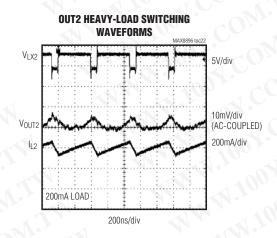


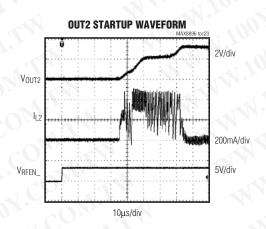
Dual PWM Step-Down Converter in a 2mm x 2mm Package for WCDMA PA and RF Power

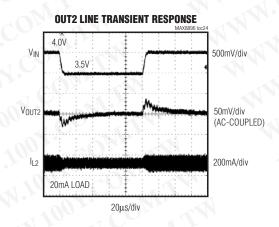
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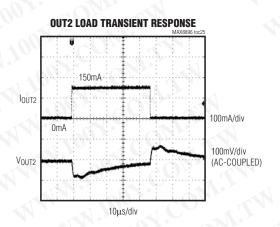
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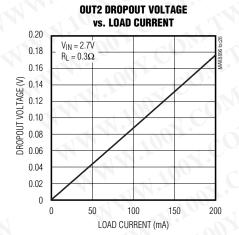








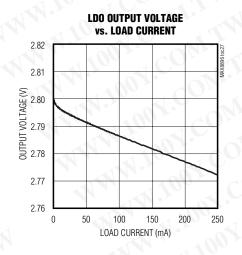


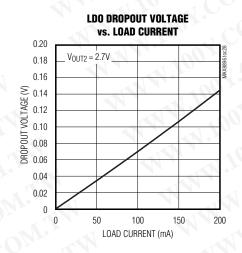


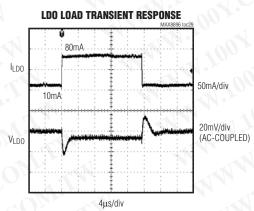
Dual PWM Step-Down Converter in a 2mm x 2mm Package for WCDMA PA and RF Power

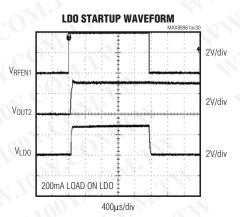
Typical Operating Characteristics (continued)

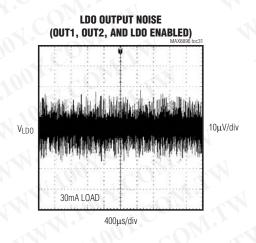
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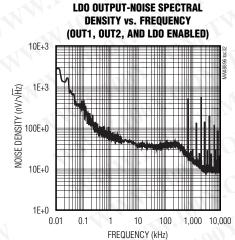












Dual PWM Step-Down Converter in a 2mm x 2mm Package for WCDMA PA and RF Power

Pin Description

PIN	NAME	FUNCTION
A1	REFBP	Reference Noise Bypass. Bypass REFBP to AGND with a $0.033\mu F$ ceramic capacitor to reduce noise on the LDO output. REFBP is internally pulled down through a $1k\Omega$ resistor during shutdown.
A2	AGND	Low-Noise Analog Ground. Connect AGND to the ground plane at a single point away from high switching currents. See the <i>PCB Layout</i> section.
A3	REFIN	DAC-Controlled Input. The output of the PA step-down converter is regulated to 2.5 x V _{REFIN} . When V _{REFIN} reaches 0.396 x V _{CC} , bypass mode is enabled.
A4	PGND1	Power Ground for OUT1. Connect PGND1 to the ground plane near the input and output capacitor grounds. See the <i>PCB Layout</i> section.
B1	LDO	200mA LDO Regulator Output. Bypass LDO with a 1µF ceramic capacitor as close as possible to LDO and ground. Leave LDO unconnected if not used.
B2	PAEN	OUT1 Enable Input. Connect PAEN to IN1 or logic-high for normal operation. Connect to ground or logic-low to shut down OUT1. Internally connected to ground through an 800kΩ resistor.
В3	RFEN2	OUT2 and LDO Enable Input. Connect RFEN1 or RFEN2 to IN2 or logic-high for normal operation. Connect RFEN1 and RFEN2 to ground or logic-low to shut down OUT2 and the LDO. Internally connected to ground through an $800k\Omega$ resistor.
B4	LX1	Inductor Connection. Connect an inductor from LX1 to the output of OUT1.
C1	OUT2	Output of OUT2. OUT2 is also the supply voltage input for the LDO. Bypass OUT2 with a 2.2µF ceramic capacitor as close as possible to OUT2 and PGND2.
C2	RFEN1	OUT2 and LDO Enable Input. Connect RFEN1 or RFEN2 to IN2 or logic-high for normal operation. Connect RFEN1 and RFEN2 to ground or logic-low to shut down OUT2 and the LDO. Internally connected to ground through an $800k\Omega$ resistor.
C3	Vcc	Supply Voltage Input for Internal Reference and Control Circuitry. Connect V _{CC} to a battery or supply voltage from 2.7V to 5.5V. Bypass V _{CC} with a 0.1µF ceramic capacitor as close as possible to V _{CC} and AGND. Connect V _{CC} , IN1, and IN2 to the same source.
C4	IN1	Supply Voltage Input for OUT1. Connect IN1 to a battery or supply voltage from 2.7V to 5.5V. Bypass IN1 with a 4.7µF ceramic capacitor as close as possible to IN1 and PGND1. Connect IN1, V _{CC} , and IN2 to the same source.
D1	PGND2	Power Ground for OUT2. Connect PGND2 to the ground plane near the input and output capacitor grounds. See the <i>PCB Layout</i> section.
D2	LX2	Inductor Connection. Connect an inductor from LX2 to the output of OUT2.
D3	IN2	Supply Voltage Input for OUT2. Connect IN2 to a battery or supply voltage from 2.7V to 5.5V. Bypass IN2 with a 2.2 μ F ceramic capacitor as close as possible to IN2 and PGND2. Connect IN2, V _{CC} , and IN1 to the same source.
D4	PAOUT	PA Connection for Bypass Mode. Internally connected to IN1 using the internal bypass MOSFET during bypass mode. PAOUT is internally connected to the feedback network for OUT1. Bypass PAOUT with a 4.7µF ceramic capacitor as close as possible to PAOUT and PGND1.

Dual PWM Step-Down Converter in a 2mm x 2mm Package for WCDMA PA and RF Power

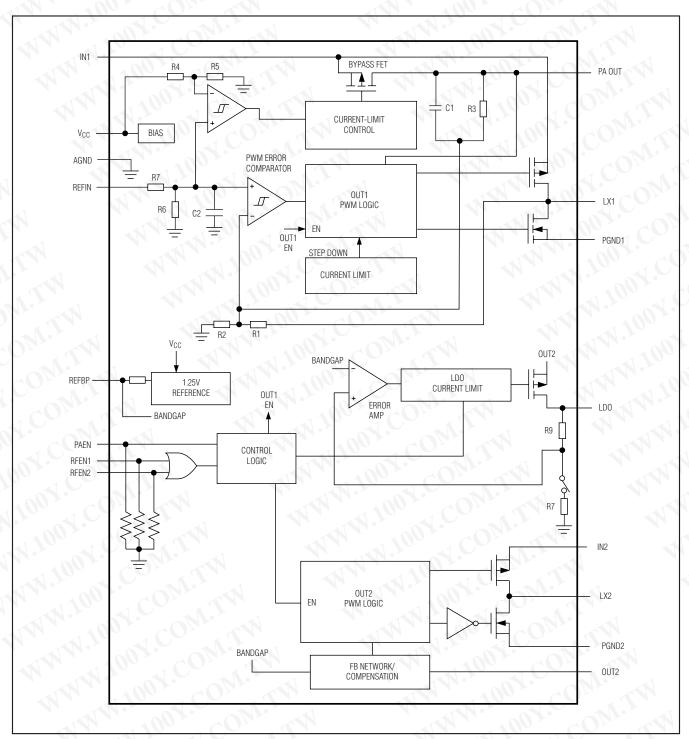


Figure 1. Block Diagram

Dual PWM Step-Down Converter in a 2mm x 2mm Package for WCDMA PA and RF Power

Detailed Description

The MAX8896 dual step-down converter is optimized for powering the power amplifier (PA) and RF transceiver in WCDMA handsets. This device integrates a highefficiency PWM step-down converter (OUT1) for medium and low-power transmission, and a $140m\Omega$ (typ) bypass FET to power the PA directly from the battery during high power transmission. A second highefficiency PWM step-down converter (OUT2) supplies power directly to a high PSRR, low-output noise, 200mA low-dropout linear regulator (LDO) to power the RF transceiver.

OUT1 Step-Down Converter

A hysteretic PWM control scheme ensures high efficiency, fast switching, fast transient response, low output ripple, and physically tiny external components. The control scheme is simple: when the output voltage is below the regulation threshold, the error comparator begins a switching cycle by turning on the high-side switch. This high-side switch remains on until the minimum on-time expires and output voltage is within regulation, or the inductor current is above the current-limit threshold. Once off, the high-side switch remains off until the minimum off-time expires and the output voltage falls again below the regulation threshold. During the off period, the low-side synchronous rectifier turns on and remains on until the high-side switch turns on again. The internal synchronous rectifier eliminates the need for an external Schottky diode.

Voltage-Positioning Load Regulation

The MAX8896 step-down converter utilizes a unique feedback network. By taking DC feedback from the LX node through R1 of Figure 1, the usual phase lag due to the output capacitor is removed, making the loop exceedingly stable and allowing the use of very small ceramic output capacitors. To improve the load regulation, resistor R3 is included in the feedback. This configuration yields load regulation equal to half the inductor's series resistance multiplied by the load current. This voltage-positioning load regulation greatly reduces overshoot during load transients or when changing the output voltage from one level to another. However, when calculating the required REFIN voltage, the load regulation should be considered. Because inductor resistance is typically well specified and the typical PA is a resistive load, the V_{REFIN} to V_{OUT1} gain is slightly less than 2.5V/V. The output voltage is approximately:

$$V_{OUT1} = 2.5 \times V_{REFIN} - \frac{1}{2} \times R_{L} \times I_{LOAD}$$

Automatic Bypass Mode

During high-power transmission, the bypass mode connects IN1 directly to PAOUT with the internal $140m\Omega$ (typ) bypass FET, while the step-down converter is forced into 100% duty-cycle operation. The low onresistance in this mode provides low dropout, long battery life, and high output current capability. OUT1 enters bypass mode automatically when VREFIN > 0.396 x VCC (see Figure 2). Current-limit circuitry continuously limits current through the bypass FET to 1000mA (typ). The bypass FET opens up if the voltage at PAOUT drops below 1.25V (typ) in current limit.

OUT2 Step-Down Converter

OUT2 is a high-efficiency, 2MHz current-mode step-down DC-DC converter that outputs 200mA with efficiency up to 94%. The output voltage of the MAX8896 is a fixed 3.1V for powering the LDO. RFEN1 and RFEN2 are dedicated enable inputs for OUT2. Drive RFEN1 or RFEN2 high to enable OUT2, or drive RFEN1 and RFEN2 low to disable OUT2. RFEN1 and RFEN2 have hysteresis so that an RC may be used to implement manual sequencing with respect to other inputs.

OUT2 operates with a constant 2MHz switching frequency regardless of output load. The MAX8896 regulates the output voltage by modulating the switching duty cycle. An internal n-channel synchronous rectifier eliminates the need for an external Schottky diode and improves efficiency. The synchronous rectifier turns on during the second half of each switching cycle (offtime). During this time, the voltage across the inductor is reversed, and the inductor current ramps down. The synchronous rectifier turns off at the end of the switching cycle.

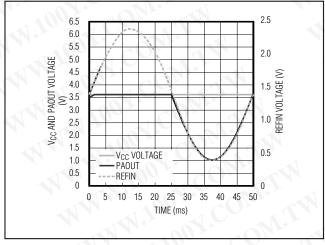


Figure 2. Automatic Bypass

Dual PWM Step-Down Converter in a 2mm x 2mm Package for WCDMA PA and RF Power

The OUT2 step-down DC-DC converter operates with 100% duty cycle when the supply voltage approaches the output voltage. This allows this converter to maintain regulation until the input voltage falls below the desired output voltage plus the dropout voltage specification of the converter. During 100% duty cycle operation, the high-side p-channel MOSFET turns on constantly, connecting the input to the output through the inductor. The dropout voltage (VDO) is calculated as follows:

 $V_{DO} = I_{LOAD} \times (R_P + R_L)$

where:

Rp = internal p-channel MOSFET switch on-resistance (see *Electrical Characteristics*)

R_I = external inductor DC resistance

LDO

The LDO provides 200mA at 2.8V and is designed for low noise ($16\mu V_{RMS}$, typ) and high PSRR (65dB, typ). The LDO is powered from OUT2 (3.1V) and is enabled or disabled at the same time as OUT2 using RFEN1 or RFEN2.

LDO Dropout Voltage

The regulator's minimum input/output differential (or dropout voltage) determines the lowest usable supply voltage. In battery-powered systems, this determines the useful end-of-life battery voltage. Because the LDO uses a p-channel MOSFET pass transistor, the dropout voltage is drain-to-source on-resistance (RDS(ON)) multiplied by the load current (see the *Typical Operating Characteristics*).

Shutdown Mode

Connect PAEN to GND or logic-low to place OUT1 in shutdown mode. In shutdown, the control circuitry, internal switching MOSFET, and synchronous rectifier turn off and LX1 becomes high impedance. Connect PAEN to IN1, VCC, or logic-high for normal operation.

Either RFEN1 or RFEN2 enable OUT2 and the LDO. Connect RFEN1 and RFEN2 to GND or logic-low to place OUT2 and the LDO in shutdown mode. In shutdown, the control circuitry, internal switching MOSFET, and synchronous rectifier turn off and LX2 and the LDO output become high impedance. Connect RFEN1 or RFEN2 to IN2, VCC, or logic-high for normal operation. When PAEN, RFEN1, and RFEN2 are all logic-low, the MAX8896 enter a very low power state, where the input current drops to 0.1µA (typ).

Thermal-Overload Protection

Thermal-overload protection limits total power dissipation in the MAX8896. If the junction temperature exceeds +160°C, the MAX8896 turn off, allowing the IC to cool. The IC turns on and begins soft-start after the junction temperature cools by 20°C. This results in a pulsed output during continuous thermal-overload conditions.

Applications Information

Inductor Selection

OUT1 operates with a switching frequency of 2MHz and utilizes a 2.2 μ H to 4.7 μ H inductor. OUT2 operates with a switching frequency of 2MHz and utilizes a 2.2 μ H inductor. This operating frequency allows the use of physically small inductors while maintaining high efficiency.

The OUT1 inductor's DC current rating only needs to match the maximum load of the application because OUT1 features zero current overshoot during startup and load transients. For optimum transient response and high efficiency, choose an inductor with DC series resistance in the $50 m\Omega$ to $150 m\Omega$ range. See Table 1 for suggested inductors and manufacturers.

Using a larger inductance value reduces the ripple current, therefore providing higher efficiency at light load.

Output Capacitor Selection

For OUT1 and OUT2, the output capacitor keeps the output voltage ripple small and ensures regulation loop stability. Cout must have low impedance at the switching frequency. Ceramic capacitors with X5R or X7R temperature characteristics are highly recommended due to their small size, low ESR, and small temperature coefficients. A 4.7µF capacitor is recommended for Cout1 and 2.2µF is recommended for Cout2. For optimum load-transient performance and very low output ripple, the output capacitor value can be increased.

For the LDO, the minimum output capacitance required is dependent on the load currents. For loads lighter than 10mA, it is sufficient to use a 0.1µF capacitor for stable operation over the full temperature range. With rated maximum load currents, a minimum of 1µF is recommended. Larger value output capacitors further reduce output noise and improve load-transient response, stability, and power-supply rejection.

Note that some ceramic dielectrics exhibit large capacitance and ESR variation with temperature and DC bias. Ceramic capacitors with Z5U or Y5V temperature characteristics should be avoided. These regulators are optimized for ceramic capacitors. Tantalum capacitors are not recommended.

Dual PWM Step-Down Converter in a 2mm x 2mm Package for WCDMA PA and RF Power

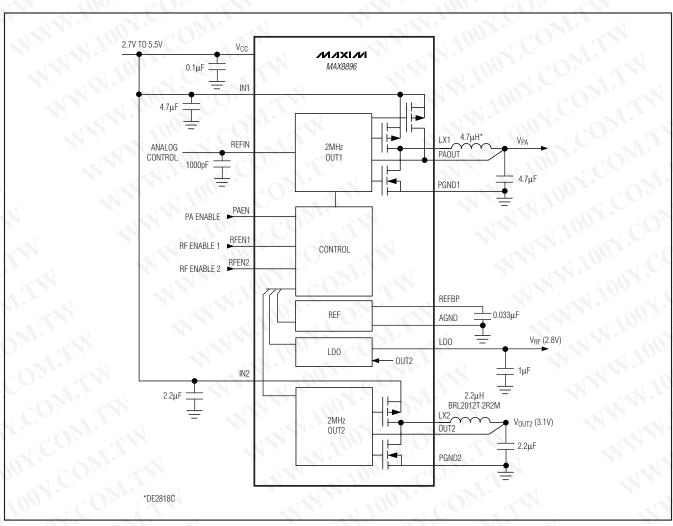


Figure 3. Typical Applications Circuit

Input Capacitor Selection

The input capacitor (C_{IN}) reduces the current peaks drawn from the battery or input power source and reduces switching noise in the MAX8896. The impedance of C_{IN} at the switching frequency should be kept very low. Ceramic capacitors with X5R or X7R temperature characteristics are highly recommended due to their small size, low ESR, and small temperature coefficients. A 4.7 μ F capacitor is recommended for C_{IN1} and 2.2 μ F for C_{IN2} . For optimum noise immunity and low input ripple, the input capacitor value can be increased.

Note that some ceramic dielectrics exhibit large capacitance and ESR variation with temperature and DC bias. Ceramic capacitors with Z5U or Y5V temperature characteristics should be avoided.

Thermal Considerations

In most applications, the MAX8896 does not dissipate much heat due to its high efficiency. But in applications where the MAX8896 runs at high ambient temperature with heavy loads, the heat dissipated may exceed the maximum junction temperature of the part. If the junction temperature reaches approximately +160°C, the thermal-overload protection is activated.

Dual PWM Step-Down Converter in a 2mm x 2mm Package for WCDMA PA and RF Power

The MAX8896 maximum power dissipation depends on the thermal resistance of the IC package and circuit board, the temperature difference between the die junction and ambient air, and the rate of airflow. The power dissipated in the device is:

 $PD = POUT1 \times (1/\eta OUT1 - 1) + POUT2 \times (1/\eta OUT2 - 1) + ILDO \times (VOUT2 - VLDO)$

where η is the efficiency of the step-down converter and POUT_ is the output power of the step-down converter. The maximum allowed power dissipation is:

$$PMAX = (TJMAX - TA)/\theta JA$$

where (T_{JMAX} - T_A) is the temperature difference between the MAX8896 die junction and the surrounding air, $\theta_{\rm JA}$ is the thermal resistance of the junction through the PCB, copper traces, and other materials to the surrounding air.

PCB Layout

High switching frequencies and relatively large peak currents make the PCB layout a very important part of design. Good design minimizes excessive EMI on the feedback paths and voltage gradients in the ground plane, resulting in a stable and well regulated output. Connect C_{IN1} close to IN1 and PGND1 and connect C_{IN2} close to IN2 and PGND2. Connect the inductor and output capacitor as close as possible to the IC and keep their traces short, direct, and wide. Keep noisy traces, such as the LX node, as short as possible. Refer to the MAX8896EVKIT for an example layout.

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Dual PWM Step-Down Converter in a 2mm x 2mm Package for WCDMA PA and RF Power

Table 1. Suggested Inductors

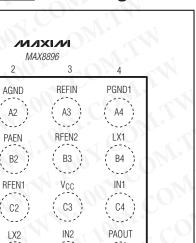
MANUFACTURER	SERIES	INDUCTANCE (µH)	ESR (Ω)	CURRENT RATING (mA)	DIMENSIONS
M.M.	CB2016T	1.0 2.2	0.09 0.13	600 510	2.0mm x 1.6 mm x 1.8 mm $= 5.8$ mm ³
Taiyo Yuden	CB2518T	2.2 4.7	0.09 0.13	510 340	2.5mm x 1.8mm x 2.0mm = 9mm ³
	BRL2012T	2.2	0.30	550	$2.0 \text{mm} \times 1.25 \text{mm} \times 1.0 \text{mn}$ = 2.5mm^3
	CKP2520	2.2	0.09	1300	2.5mm x 2.0mm x 1.0mm = 5mm ³
FDK	MIPF2520	1.0 1.5 2.2	0.05 0.07 0.08	1500 1500 1300	2.5mm x 2.0mm x 1.0mm = 5mm ³
	MIPF2016	2.2	0.11	1100	2.0mm x 1.6mm x 1.0mm = 3.2mm ³
Murata	LQH32C_53	1.0 2.2	0.06 0.10	1000 790	3.2mm x 2.5mm x 1.7mm = 14mm ³
W.T.N	D3010FB	1.0	0.20	1170	3.0mm x 3.0mm x 1.0mm = 9mm ³
	D2812C	1.2 2.2	0.09 0.15	860 640	$3.0 \text{mm} \times 3.0 \text{mm} \times 1.2 \text{mm}$ = 11mm^3
токо	D310F	1.5 2.2	0.13 0.17	1230 1080	3.6mm x 3.6mm x 1.0mm = 13mm ³
	D312C	1.5 2.2	0.10 0.12	1290 1140	3.6mm x 3.6mm x 1.2mm = 16mm ³
	DE2818C	4.7	72	950	3.2mm x 3.0mm x 1.8mm = 17.3mm ³
100x.co	CDRH2D09	1.2 1.5 2.2	0.08 0.09 0.12	590 520 440	3.0mm x 3.0mm x 1.0mm = 9mm ³
Sumida	CDRH2D11	1.5 2.2 3.3	0.05 0.08 0.10	680 580 450	3.2mm x 3.2mm x 1.2mm = 12mm ³
Coilcraft	LPO3310	1.0 1.5 2.2	0.07 0.10 0.13	1600 1400 1100	3.3mm x 3.3mm x 1.0mm = 11mm ³
WWW	XPL2010	4.7	0.284	740	1.9mm x 2.0mm x 1.0mm = 3.8mm ³
WW	ELC3FN	1.0 2.2	0.08 0.12	1400 1000	3.2mm x 3.2mm x 1.2mm = 12mm ³
Panasonic	ELL3GM	1.0 2.2	0.07 0.10	1400 1100	3.2mm x 3.2mm x 1.5mm = 15mm ³

NIXIN

MAX8896

Dual PWM Step-Down Converter in a 2mm x 2mm Package for WCDMA PA and RF Power

Pin Configuration



D4

D3

16-BUMP UCSP

_____Chip Information

PROCESS: BICMOS

Package Information

For the latest package outline information and land patterns, go to www.maxim-ic.com/packages.

PACKAGE TYPE	PACKAGE CODE	DOCUMENT NO.
16 UCSP	R162A2+1	21-0226

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TOP VIEW (BUMPS ON BOTTOM)

В

С

REFBP

A1

LD0

B1

OUT2

C1

PGND2

D1 :

D2